

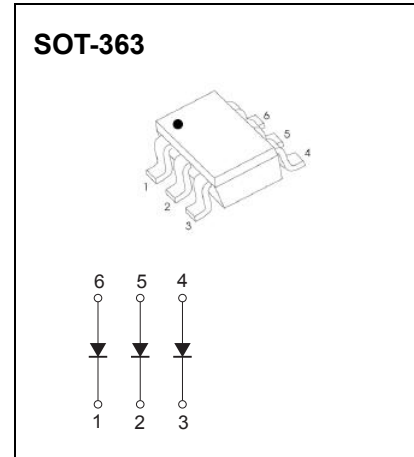
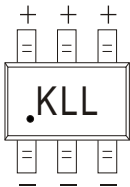
## Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE

### FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Fast Switching
- Low Leakage Current

### MARKING: KLL



### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

		Limit	Unit
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$	40	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	$I_{FM}$	350	mA
Average Rectified Current	$I_O$	175	mA
Non-repetitive Peak Forward Surge Current@t=8.3ms	$I_{FSM}$	2	A
Power Dissipation	$P_d$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	°C/W
Junction Temperature	$T_j$	125	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

### Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	40			V	$I_R=100\mu A$
Forward voltage	$V_F$			0.37 0.50	V	$I_F=20mA$ $I_F=100mA$
Reverse current	$I_R$			2.0 5.0	$\mu A$	$V_R=10V$ $V_R=30V$
Capacitance between terminals	$C_T$		50		pF	$V_R=0V, f=1.0MHz$
Reverse recovery time	$t_{rr}$		10		ns	$I_F=I_R=200mA$ $I_{rr}=0.1I_R, R_L=100\Omega$



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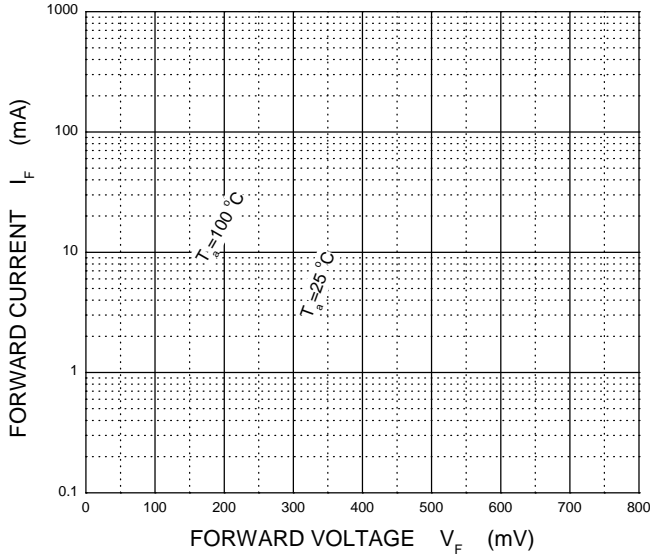


**SD103ADW**

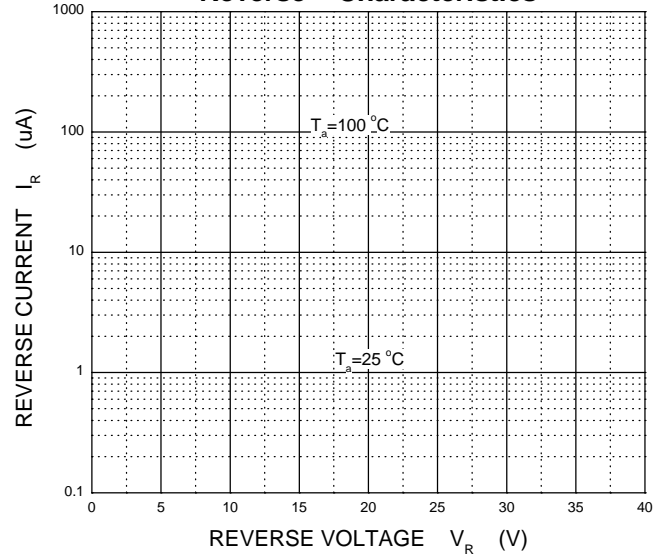
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**Typical Characteristics**

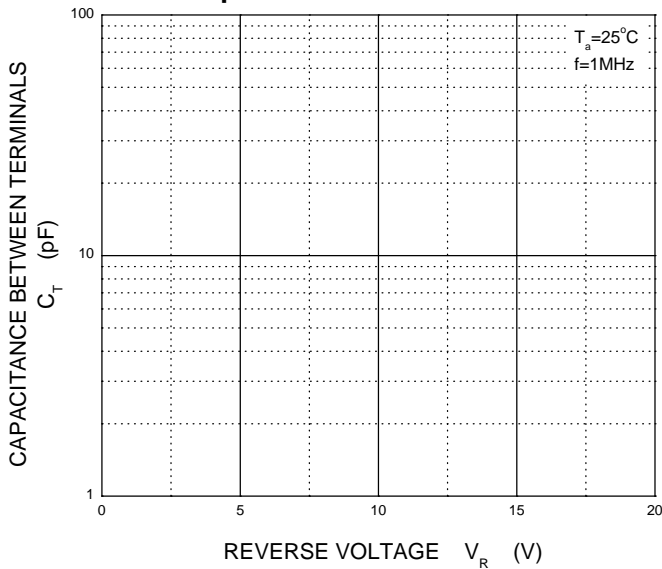
**Forward Characteristics**



**Reverse Characteristics**



**Capacitance Characteristics**



**Power Derating Curve**

